

Title (en)
VERTICAL TRANSISTOR COMPRISING A MOBILE GATE AND A METHOD FOR THE PRODUCTION THEREOF

Title (de)
VERTIKAL-TRANSISTOR MIT BEWEGLICHEM GATE UND VERFAHREN ZU DESSEN HERSTELLUNG

Title (fr)
TRANSISTOR VERTICAL A GRILLE MOBILE ET SON PROCEDE DE PRODUCTION

Publication
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Application
EP 01936280 A 20010426

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• EP 0104702 W 20010426

Abstract (en)
[origin: DE10029501C1] Vertical field effect transistor made from a semiconductor wafer comprises a residual transistor consisting of a source region (42), a channel region (3), a drain region (1), and a moving gate structure (8) made from the semiconductor material arranged before the channel region. An Independent claim is also included for a process for producing a field effect transistor comprising defining the source, drain and channel regions of the residual transistor by forming doping layers in or on a semiconductor wafer; and defining the moving gate structure by isotropic and/or anisotropic etching. Preferred Features: The wafer material is single crystalline silicon. The residual transistor consists of vertical coated regions of different doping.

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B81B 3/00; **H01L 29/84**; **G01P 15/12**; **G01L 9/00**; **B81C 1/00**

IPC 8 full level
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